



# CSUN-S156-5BB(Dia210)

HIGHER EFFICIENCY MONOCRYSTALLINE SILICON SOLAR CELLS

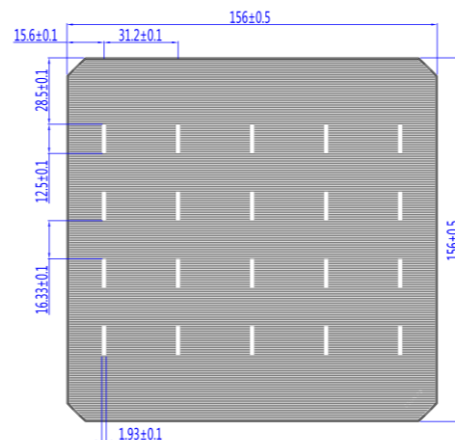
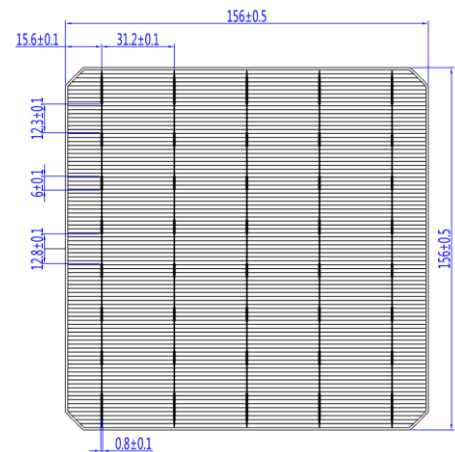
## PERC

### MECHANICAL DATA AND DESIGN

Format	156mm×156mm±0.5mm
Thickness	200um±20um
Front(-)	0.8mm bus bars (silver), blue anti-reflecting coating (silicon nitride)
Back(+)	1.93mm wide soldering pads (silver) back surface field (aluminum)

### FEATURES

- Higher cell efficiency and higher electricity power output
- Superior light trapping effect, excellent rear side passivation & local metalization technology, and advanced passivated & uniform emitter process can ensure higher and uniform full-wavelength spectrum response
- Innovative 5-busbar front metallization design obtains more concentrated cell efficiency distribution, less module power loss and good PV system reliability
- Excellent performance in weak light environments
- Lower temperature coefficient
- Excellent anti-PID performance
- Thinner silicon substrate and lower production cost



Class	Efficiency(%)	Pmpp(W)	Umpp(V)	Impp(A)	Uoc(V)	Isc(A)	FF(%)
20.70%	20.70-20.80	5.03	0.567	8.87	0.663	9.54	79.51
20.60%	20.60-20.70	5.01	0.565	8.86	0.661	9.50	79.73
20.50%	20.50-20.60	4.98	0.564	8.82	0.660	9.51	79.23
20.40%	20.40-20.50	4.95	0.562	8.81	0.658	9.51	79.18
20.30%	20.30-20.40	4.93	0.560	8.81	0.656	9.56	78.69
20.20%	20.20-20.30	4.90	0.558	8.78	0.654	9.48	79.06
20.10%	20.10-20.20	4.88	0.558	8.75	0.654	9.48	78.87
20.00%	20.00-20.10	4.86	0.556	8.74	0.652	9.49	78.50
19.90%	19.90-20.00	4.83	0.554	8.72	0.650	9.48	78.41

### STANDARD TEST CONDITION (STC)

Light Intensity	1000W/m <sup>2</sup>
Spectrum	AM 1.5G
Temperature	25°C

### TEMPERATURE COEFFICIENTS

TkVoltage	-0.30%/K
TkCurrent	+0.04%/K
TkPower	-0.40%/K

### IV Curve

